COST Action TUMIEE (CA17126) - 18th July 2022, Crete.

Ultrafast Transient Absorption Spectroscopy of Some Potential EUV Resist Molecules

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Ultrafast Transient Absorption Spectroscopy of an EUV Candidate Resist Molecule

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Firstly



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- We are an Intense Laser Matter Interactions Group
- Laser Plasma Diagnostics (Optical & Particle)
- Laser Plasma Spectroscopy (UV, VUV and EUV)
- Dual Laser Plasma Photoabsorption (VUV & EUV)
- Photoionization in Ultrafast FEL (or FEL + IR) Fields
- UTAS is a completely new option & technique for us
- So, I'm talking about something I know little about
- For a reason....

Motivation

Ollscoil Chathair Bhaile Átha Cliath Dublin City University Huge number of synthesis + steady state analysis resist papers published over more than two decades now

Analysis mainly using NMR and FTIR but also UV-Vis and MS Little done/known about dynamics on a femtosecond timescale Industry has many questions about dynamics Very large nvestments (being) made in IMEC¹ and ARCNL² EUVL (being) rolled out e.g., in TSMC and INTEL (FAB 34 -Ireland)³

So, collaboration established with synthetic chemistry colleagues (funded by SFI exploratory grant)

- 1. https://www.kmlabs.com/news-and-events/icaleo-2020
- 2. https://arcnl.nl/research-groups/high-harmonic-generation-and-euv-science
- 3. https://www.eenewseurope.com/en/asml-ships-euv-scanner-to-irish-fab

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Sample Industry Questions

- Are there good and bad ways to increase photon absorption?
- How many electrons can the resist use for good chemistry?
- Are all electrons created equal (e.g., Photo vs Auger)?
- What are the e-driven reactions occurring in the resist?
- Are they competing reactions?
- Can reactions be controlled (even suppressed)?

 One also needs to understand chemical noise (stochastic effects) and its effect on e.g., LER/LWR

In summary

Radiation chemistry fundamentals (experiment and modeling) are believed to be the way forward to enhance photoresist design - 'waferbased learning is no longer sufficient'

Talk Outline

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- EUVL Some Fundamentals
- EUVL Current Candidate Resist Types
- UTAS Experimental Setup
- (Very) Preliminary Measurements
- Perspective

Photolithography Process

Silicon wafer We begin with a clean silicon wafer spin coated with photoresist

Photomask A glass or mylar mask coated with an opaque film defines the features

Exposure

A mask aligner is used to pass UV light through the mask onto the wafer

Development

Exposed resist is washed away while unexposed resist remains

https://www.brewerscience.com/products/advanced-lithography/

Deposition

Metallic, semiconductor or insulating layers are evaporated or sputtered onto the surface

Wet or Dry Etch Exposed sections are etched away while the resist protects the remaining areas Liftoff Photoresist is removed, leaving behind precisely deposited features

Resist Removal Photoresist is removed, leaving behind precisely etched features

 $Resolution = k.\frac{\lambda}{NA}$

 $K_{typ.} \sim 0.25$

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- Photolithography is a key step in the manufacture of ICs
- Uses light to imprint patterns (think of it as old style photographic recording)
- A photoresist is a light sensitive material, applied to the surface (the emulsion)
- When exposed to light, it undergoes a solubility change - (de)protection
- The resist can become more soluble (positive tone) via fragmentation or less soluble (negative tone) through cross-linking or polymerization.

Global Extreme Ultraviolet Lithography EUVL Systems Market Research Report 2022 - https://www.researchandmarkets.com

Current Standard: UV Immersion Lithography

Theoretical limit for 193 nm lithography, i.e., 36 nm halfpitch patterning, has been reached

Usage of double and triple patterning techniques has extended UV(I)L shelf-life, but has also resulted in an increase in manufacturing steps and costs

RSC Adv., 2020, 10, 8385-8395 - DOI: 10.1039/C9RA08977B

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Some Fundamentals

VS

EUV (13.5 nm)

Absorption at the (Sn) 13.5 nm wavelength Carried out in vacuum

Allows for printing of patterns X14 smaller than with 193 nm (Rayleigh criterion)

EUV Lithography (EUVL) will allow for sub-7 nm patterned circuits

Absorption at the (ArF) 193 nm wavelength

Wafers immersed in water during manufacture

Improves resolution by ~refractive index of the liquid component

Allows for double or triple patterning

RLS targets:

- Resolution: <20nm
- Line Edge Roughness (LER): <20% (nm)
- Sensitivity (D₀): <20 mJ cm⁻²
- RLS Displayed as Triangles

Figure of Merit: $Z = D_0 x (LER)^2 x (HP)^3 (mJ/nm^3)$

NP (MOx): Nanoparticle Resists (https://www.inpria.com)
 HSQ: Hydrogen Silsesquioxane Resists (non-CAR, https://www.aqmaterials.com)
 CAR: Chemically Amplified Resist (https://www.jsrmicro.be)

Proc. SPIE 7972, 797202 (2011) / https://doi.org/10.1117/12.882955

Current Candidate Resist Types

Currently – four resist types under investigation for EUVL

1. Chemically Amplified (CAR)

2. Nanoparticle (NPR)

3. Multi-Trigger (MTR)

4. Organo-Metallic (OMR)

Current Candidate Resist Types

Invented by IBM research to increase the resist sensitivity of Diazonaphthoquinone (DNQ) or Novolac*

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- An acid amplifier is a compound added to improve RLS performance of photoresists. It works in conjunction with a photoacid generator
- The photoacid generator (PAG) is a molecular group that generates acids can then defuse into the polymer chain and catalyses the deprotection of the side groups, which in turn leads to a reduction in the energy requirement of the photoinduced reaction. This lowers the dose of 13.5 nm required improving the sensitivity of the polymer
- Acid seepage, leading to poor LER/LWR values is the main weakness

* VLSI Technology, 1982. Digest of Technical Papers. Symposium on, pp. 86-87, Sept 1982.
Muyoung Kim et al., Macromolecules **51**, pp6922–6935 (2018)

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Current Candidate Resist Types

Nanoparticle (MOx) Resists (https://www.inpria.com)

Methacrylic acid (MAA) modified zirconium (or hafnium) oxide nanoparticles (ZrO₂ -MAA-NP or HfO₂ -MAA-NP) tend to produce the best over-all RLS performance

N Thakur et al. J Mater Chem C. Vol. 8, pp. 14499-14506 (2020).

H Xu et al., Proc. SPIE 10583, 105831P (2018) https://doi.org/10.1117/12.2297266

M Krysak et al. Proc SPIE 9048, 904805-1 (2014) https://doi.org/10.1117/12.2046677

- CARs are slowly being phased out and replaced with nanoparticle resists (NPRs). Commercial NPRs are (currently) based on a tin or hafnium- oxide NPs
- Zinc-oxide based nanoparticles possess small size, good solubility in spin-coating solvents, good film-forming ability, but moderate pattering performance under deep-UV irradiation
- EUV light hits exposed resist area
- EUV light is absorbed by the ligands (photoacid spikes)
- The ligands join with the neighbouring nanoparticle if the neighbour nanoparticle has also absorbed a photon.
- The exposed resist area hardens, and the unexposed area is washed away by aqueous developer
- The final resist pattern has sharp edges and very sturdy features due to the metallic core of tin or hafnium.

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Current Candidate Resist Types

Multi-Trigger Resists (https://irresistiblematerials.com)

Negative-tone crosslinking resist Post Exposure Bake (Not required) High Spatial Resolution (R) and Low Line-Edge Roughness (LER) values

Journal of Photopolymer Science and Technology. Vol 31, pp 227-232 (2018).

- EUV photons produce 'initiators' (e.g., acid species) in the PAG
- The initiators activate the resist molecules
- If two activated resist molecules are adjacent, they react and releases the initiators (Figure, Top Panel).
- If two activated resist molecules are not adjacent, then the initiators remain bound and there is no reaction (Figure, Bottom Panel).
- This mechanism prevents acid species moving away from its initial location (this problem happens in CARs and nanoparticle resists), thus helping MTRs achieve higher resolution and lower LER values in comparison to NPRs and CARs.

Current Candidate Resist Types

OMRs - Pd Oxalate: DPPM-Pd-C₂O₄

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Fig. 4 $L_2M(C_2O_4)$ and $L_2M(CO_3)$ evaluated for EUV sensitivity. (a) Platinum and palladium carbonates showing negative-tone behavior. (b) Platinum and palladium oxalates showing positive-tone.

1,1-Bis(diphenylphosphino)methane (dppm), - CH₂(PPh₂)₂

Miriam Sortland et al., J. Micro/Nanolith. MEMS MOEMS 14, Art. No. 043511 (2015)

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Current Candidate Resist Types

OMRs – Pd/Pt Oxalates (vs Carbonates & Azides) Findings – Sortland et al.

- Many platinum & palladium complexes show little or no EUV sensitivity
- Metal carbonates and metal oxalates ($L_2M(CO_3)$) and $L_2M(C_2O_4)$; M Pt or Pd) are sensitive to EUV
- Palladium-based resists are more sensitive than platinumbased resists – compare 21 with 23 (Fig 4, previous slide)
- Photo-mechanistic studies to date on L2M(C2O40 in the literature are experimental, at long wavelengths, in solution and usually not in air

Miriam Sortland et al., J. Micro/Nanolith. MEMS MOEMS 14, Art. No. 043511 (2015)

Current Candidate Resist Types

OMRs - Pd Oxalate: Photo-Mechanism (Summary)

- Exposing L₂PdC₂O₄ to an EUV photon results in the reductive elimination of 2 equivalences of CO₂ and the formation of a reactive intermediate L₂Pd
- The L₂Pd reacts with another L₂PdC₂O₄ (resist) molecule to form a zerovalent L₂PdL₂ complex, leaving behind a bare Pd metal atom and 2 x CO₂ i.e., remaining Pd-DPPM complex reforms bond to another complex (Pd-Pd)

$$2 L_2 Pd \overbrace{0}^{0} \overbrace{0}^{0} + 2 L_2 PdL_2 + Pd(0) + 4 CO_2$$

Miriam Sortland et al., J. Micro/Nanolith. MEMS MOEMS 14, Art. No. 043511 (2015)

OMRs - Pd Oxalate: DPPM-Pd-C₂O₄ (Summary Performance)

E _{size} (mJ/cm ²) LER (nm)					
(a)	156 5.1 50	156 8.0 35	156 25	156 22	
(b)	90 6.8 50	90 5.2 40	90 5.5 30	90 22	
(c)	90 8.3 50	140 6.0 40	50 7.5 30	50 22	Г Г

CD (nm)

- Positive tone photoresist
- Exhibits good performance,
 <30 nm half-pitch

Ph

Ph

Sample 23:

(a) Developer: 10% methyl isobutyl ketone (MIBK)/ toluene, on underlayer.

(b) Developer: 10% MIBK/toluene, no underlayer.

(c) Developer: 20% MIBK/ toluene, no underlayer.

Miriam Sortland et al., J. Micro/Nanolith. MEMS MOEMS **14**, Art. No. 043511 (2015)

Any (Multi-Scale) Modelling Available?

Muyoung Kim et al., Macromolecules 51, pp6922-6935 (2018)

Positive tone-chemically amplified resist (CAR), poly(hydroxystyrene-co-[tert-butoxycarbonyl]oxystyrene), or P(HOSt-co-tBOCSt)

PAG, triphenylsulfonium triflate (TPS-tf), loaded by 5.68–30.12 wt% of the resist

Fig. 10 LER variation with PAG concentration 5.68-30.12 wt%

UTAS Experimental Setup

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UF Spectroscopy Laboratory

Astrella 30 fs /7 mJ / KHz Regen Amplifier (800/ 400/ 267 nm)

OPAs: 0.2- 2 μm & 2 – 12 μm

Transient 2D-IR (Phasetech) & Newport TAS (350 – 900 nm)

Newport TAS

UTAS Experimental Setup

UTAS Experimental Setup Phenomena occurring during TA

Ground State Bleaching (GSB) Simulated Emission (SE) Induced Absorption (IA)

Very Preliminary Measurements

Ollscoil Chathair Bhaile Átha Cliath Dublin City University Commercial Resists: Solvent: Acetone, OD_{400nm}: 1 nLOF 2020M - CAR - Negative Tone - h & i line sensitive

AZ ECI 3007 - CAR - Positive Tone - g, h & i line sensitive

AZ 1505 - CAR - Positive Tone - g, h & i line sensitive

Synthesized: Solvent: Dimethylformamide (DMF), OD_{400nm}: 1 Palladium Oxalate DPPM - Positive Tone – EUV line sensitive

Very Preliminary Measurements (nLOF 2020)

Very Preliminary Measurements (AZ ECI 3007)

Very Preliminary Measurements (AZ 1505)

Experimental Data

Global Fit

100

120

140

2 Lifetimes: 600fs, 42ps

Very Preliminary Measurements (DPPM Pd C₂O₄)

Very Preliminary Results – Time Resolved Spectroscopy

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- Fell into this line of research but looks promising scientifically
- Many candidate resists but the industry is trying to extend CAR use
- Strong (ΔD) signals for 400 nm pump in all samples to date
- Puzzle no response for 267 nm pump?
- Calculations on the electronic structure of Pd-Oxalate are needed now to help with UTAS pump selection(searching literature)
- We have some access to ICHEC (Gaussian 16) & ORCA
- But TDDFT level at best
- Into the (near/midterm) future we will explore laser ablation nanoparticle formation in e.g., MMA based resists for NPRs

People

Ireland

Stephen Durkan

Lazaros Varvarezos

Mary Pryce

Matt Shaw

P.R.O ROSS MCGARRY

PGAC COMMITTEE 2021/22

Ross McGarry

Extra Slides

Very Preliminary Measurements (UV-Vis)

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Weak absorption at 400 nm Strong UTAS signals for all samples Possibly a multiphoton excitation

Standoff LIBS Prototype – Under Construction

Top view showing double pulse laser setup with telescope.

Split tables with laser PSUs

Spectrometers for WP1 1. Time-Gated 2. Continuous-Readout 3. Wide-Spectral Range

VUV LIBS (and Photoabsorption)

Dual Pulse Vacuum-UV (VUV) LIBS Lab.

Laser Plasma (Optical) Diagnostics Lab

Stephen Durkan / Séamus Cummins/ James Campbell - all PhD students

Lazaros Varvarezos (PD)

Ultrafast (UF) Laser Spectroscopy Lab

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WP4. UF Laser Spectroscopy Laboratory @ DCU

WP4. Inside the UF Transient Spectrometer

WP4. UF Laser Table with Astrella Amplifier & OPAs

WP4. UF Time Resolved IR Spectrometer